IN THE CLAIMS:

A complete listing of all the claims is now presented.

Claims 1 - 12. (Cancelled).

Claim 13. (Currently Amended).

A semiconductor wafer, comprising

a substrate wafer made of monocrystalline silicon and an epitaxial layer deposited thereon;

said substrate wafer having a resistivity of from 0.1 to 50 Ωcm, an oxygen concentration of less than $7.5*10^{17}$ $atcm^{-3}$ and a nitrogen concentration of from $1*10^{13}$ to $5*10^{15}$ $atcm^{-3}$; and

the epitaxial layer has a thickness of from 0.2 to 1.0 µm and has a top surface on which fewer than 30 LLS defects with a size of more than 0.085 µm can be detected.

Claim 14. (Previously Presented).

The semiconductor wafer as claimed in claim 13,

wherein the oxygen concentration of the substrate wafer is less than $6.5*10^{17}$ $atcm^{-3}$.

Claim 15. (Previously Presented) .

The semiconductor wafer as claimed in claim 13,

wherein the nitrogen concentration of the substrate wafer

lies in a range of from $1*10^{14}$ to $5*10^{14}$ $atcm^{-3}$.

Claims 16 to 24 (Cancelled).

Claim 25. (Currently Amended).

A semiconductor wafer consisting of

a substrate wafer made of monocrystalline silicon and an epitaxial layer deposited thereon;

said substrate wafer having a resistivity of from 0.1 to 50 Ωcm, an oxygen concentration of less than $7.5*10^{17}$ $atcm^{-3}$ and a nitrogen concentration of from $1*10^{13}$ to $5*10^{15}$ $atcm^{-3}$; and

the epitaxial layer has a thickness of from 0.2 to 1.0 µm and has a top surface on which fewer than 30 LLS defects with a size of more than 0.085 µm can be detected.

Claim 26. (Previously Presented).

The semiconductor wafer as claimed in claim 25,

wherein the oxygen concentration of the substrate wafer is less than $6.5*10^{17}$ $atcm^{-3}$.

Claim 27. (Previously Presented).

The semiconductor wafer as claimed in claim 25,

wherein the nitrogen concentration of the substrate wafer lies in a range of from $1*10^{14}$ to $5*10^{14}$ $atcm^{-3}$.